

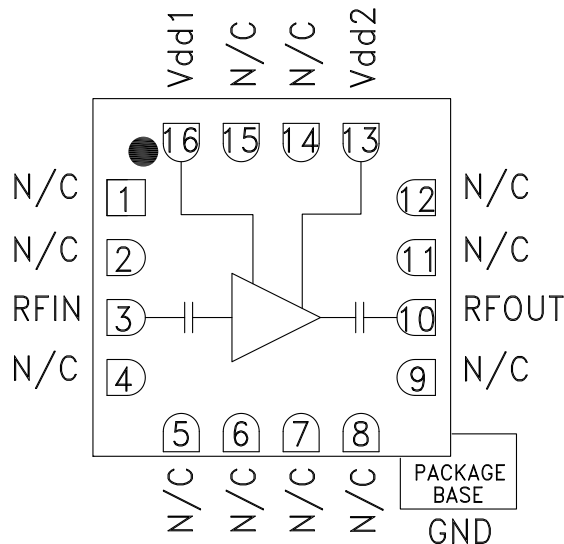
GAAS PHEMT MMIC MEDIUM POWER AMPLIFIER, 5 - 20 GHz

Typical Applications

The HMC451LC3 is ideal for use as a medium power amplifier for:

- Microwave Radio & VSAT
- Military & Space
- Test Equipment & Sensors
- Fiber Optics
- LO Driver for HMC Mixers

Functional Diagram



Features

- Gain: 19 dB
- Saturated Power: +21 dBm @ 21% PAE
- Output IP3: +30 dBm
- Single Supply: +5V @ 114 mA
- 50 Ohm Matched Input/Output
- RoHS Compliant 3 x 3 mm SMT package

General Description

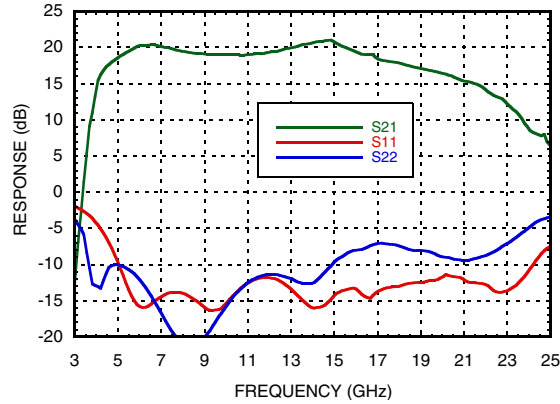
The HMC451LC3 is an efficient GaAs PHEMT MMIC Medium Power Amplifier housed in a leadless RoHS compliant SMT package. Operating between 5 and 20 GHz, the amplifier provides 19 dB of gain, +21 dBm of saturated power and 21% PAE from a single +5V supply. This 50 Ohm matched amplifier does not require any external components and the RF I/O's are DC blocked, making it an ideal linear gain block or driver for HMC SMT mixers. The HMC451LC3 allows the use of surface mount manufacturing techniques.

Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_{dd1} = V_{dd2} = +5\text{V}$

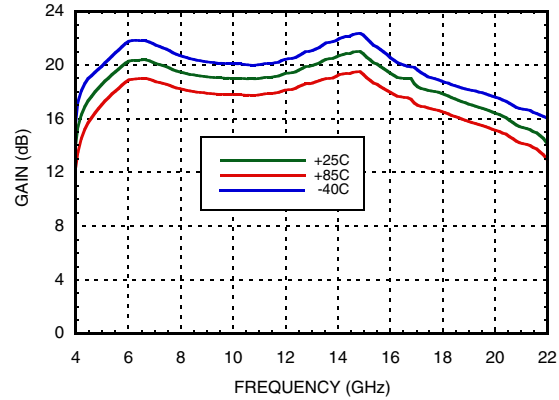
Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range	5 - 15			15 - 18			18 - 20			GHz
Gain	16	19		15	18		14	17		dB
Gain Variation Over Temperature		0.015	0.025		0.015	0.025		0.015	0.025	dB/°C
Input Return Loss		13			13			12		dB
Output Return Loss		12			8			8		dB
Output Power for 1 dB Compression (P1dB)	16.5	19.5		16	19		16.5	19.5		dBm
Saturated Output Power (Psat)		21			20.5			21		dBm
Output Third Order Intercept (IP3)		32			29			29		dBm
Noise Figure		7			6.5			7		dB
Supply Current (Idd)		114			114			114		mA

GAAS PHEMT MMIC MEDIUM POWER AMPLIFIER, 5 - 20 GHz

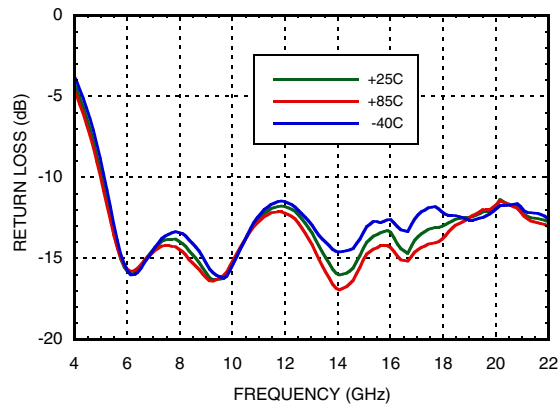
Broadband Gain & Return Loss



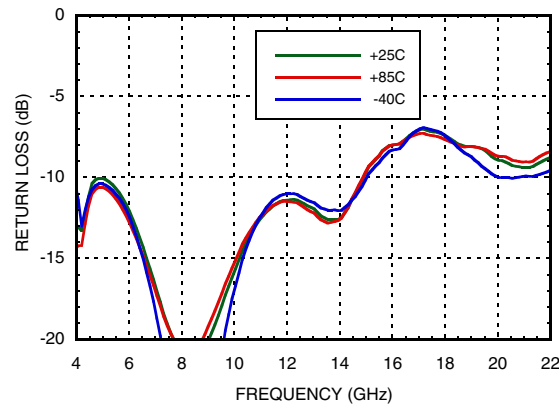
Gain vs. Temperature



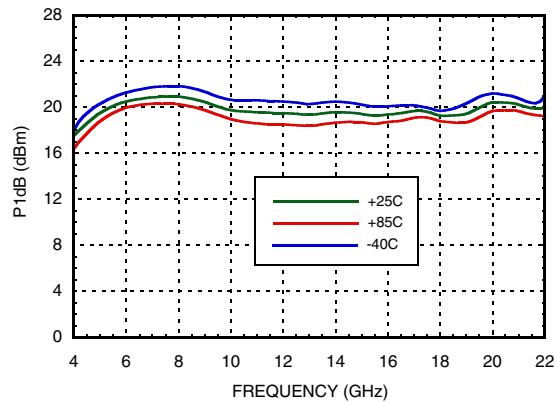
Input Return Loss vs. Temperature



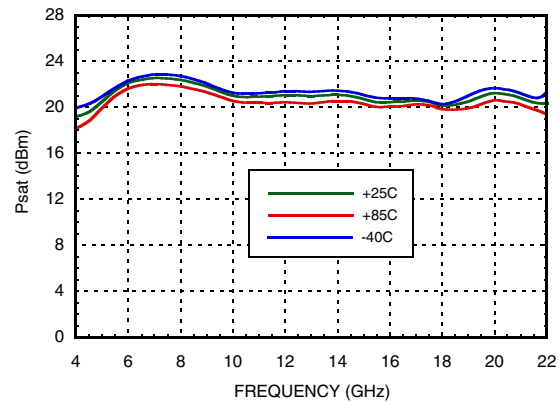
Output Return Loss vs. Temperature



P1dB vs. Temperature

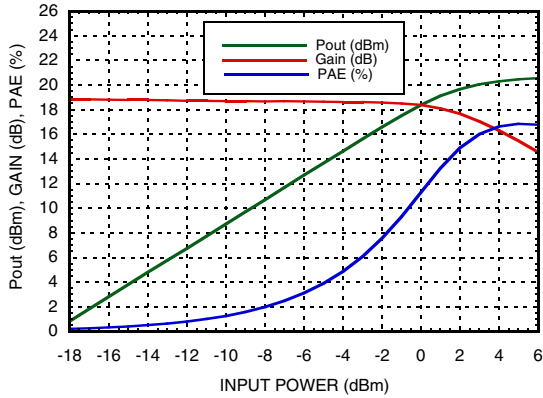


Psat vs. Temperature

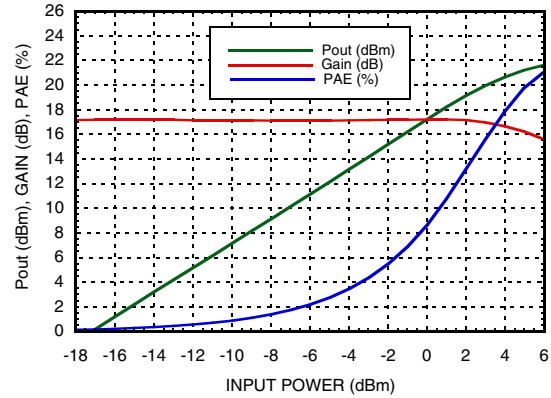


GAAS PHEMT MMIC MEDIUM POWER AMPLIFIER, 5 - 20 GHz

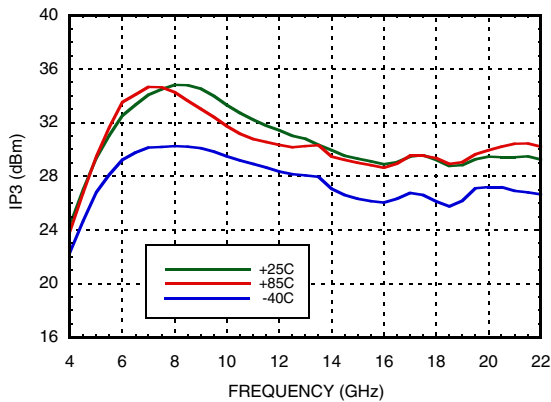
Power Compression @ 10 GHz



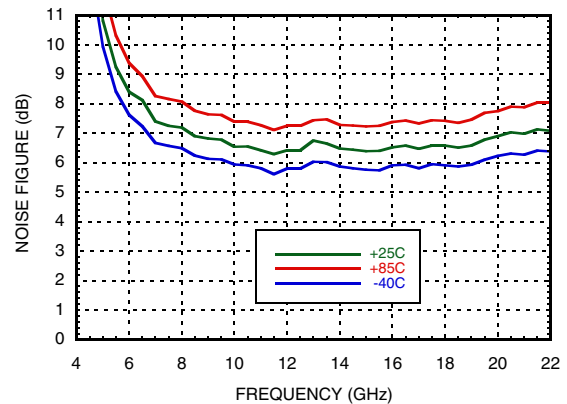
Power Compression @ 20 GHz



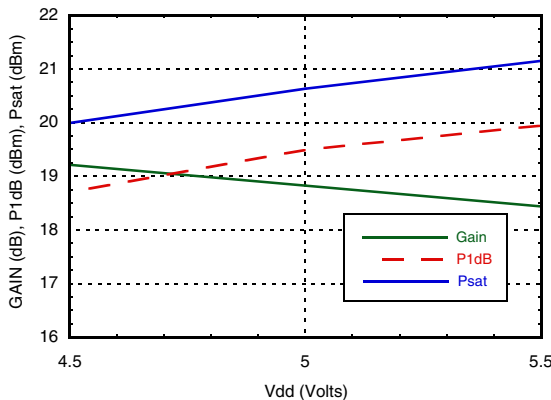
Output IP3 vs. Temperature



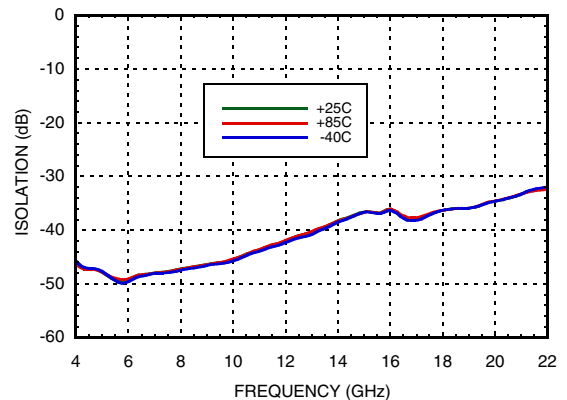
Noise Figure vs. Temperature



Gain, P1dB & PSAT vs. Supply Voltage @ 11 GHz



Reverse Isolation vs. Temperature



GAAS PHEMT MMIC MEDIUM POWER AMPLIFIER, 5 - 20 GHz

Absolute Maximum Ratings

Drain Bias Voltage ($V_{dd1} = V_{dd2}$)	+5.5 Vdc
RF Input Power (RFIN)($V_{dd} = +5V_{dc}$)	+10 dBm
Channel Temperature	175 °C
Continuous P_{diss} ($T = 85$ °C) (derate 12.4 mW/°C above 85 °C)	1.1 W
Thermal Resistance (channel to ground paddle)	80 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A, passed 250V

Typical Supply Current vs. $V_{dd1} = V_{dd2}$

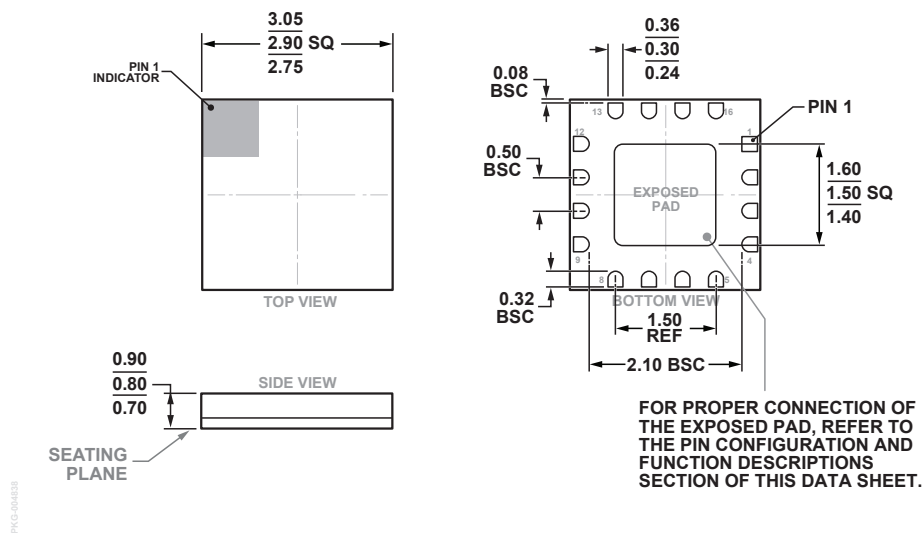
$V_{dd1} = V_{dd2}$ (V)	$I_{dd1} = I_{dd2}$ (mA)
+4.5	111
+5.0	114
+5.5	116

Note: Amplifier will operate over full voltage range shown above



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



16-Terminal Ceramic Leadless Chip Carrier [LCC]
(E-16-1)
Dimensions shown in millimeters.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[2]
HMC451LC3	Alumina, White	Gold over Nickel	MSL3 ^[1]	H451 XXXX

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

GAAS PHEMT MMIC MEDIUM POWER AMPLIFIER, 5 - 20 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4 - 9, 11, 12, 14, 15	N/C	This pin may be connected to RF/DC ground. Performance will not be affected.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms from 5 - 20 GHz.	
10	RFOUT	This pin is AC coupled and matched to 50 Ohms from 5 - 20 GHz.	
13	Vdd2	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1,000 pF and 2.2 μF are required.	
16	Vdd1	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1,000 pF and 2.2 μF are required.	
	GND	Package bottom must be connected to RF/DC ground.	

Application Circuit

Component	Value
C1, C2	100 pF
C3, C4	1,000 pF
C5, C6	2.2 μF

